

RELIABILITY REPORT
FOR
MAX836EUS+
PLASTIC ENCAPSULATED DEVICES

December 9, 2011

MAXIM INTEGRATED PRODUCTS

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Approved by
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Quality Assurance
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Conclusion

The MAX6225BESA+ successfully meets the quality and reliability standards required of all Maxim products. In addition, Maxim's continuous reliability monitoring program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards.

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I. Device Description

A. General

The MAX836/MAX837 micropower voltage monitors contain a 1.204V precision bandgap reference and a comparator in a SOT143 package. The MAX836 has an open-drain, N-channel output driver, while the MAX837 has a push-pull output driver. Two external resistors set the trip threshold voltage.

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II. Manufacturing Information

A. Description/Function:	4-Pin Micropower Voltage Monitors
B. Process:	S3
C. Number of Device Transistors:	
D. Fabrication Location:	Oregon
E. Assembly Location:	Thailand
F. Date of Initial Production:	Pre 1997

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III. Packaging Information

A. Package Type:	4L SOT
B. Lead Frame:	Copper
C. Lead Finish:	100% matte Tin
D. Die Attach:	Conductive
E. Bondwire:	Au (1 mil dia.)
F. Mold Material:	Epoxy with silica filler
G. Assembly Diagram:	#05-1601-0019 / A
H. Flammability Rating:	Class UL94-V0
I. Classification of Moisture Sensitivity per JEDEC standard J-STD-020-C	1
J. Single Layer Theta Ja:	N/A
K. Single Layer Theta Jc:	N/A
L. Multi Layer Theta Ja:	290°C/W
M. Multi Layer Theta Jc:	100°C/W

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IV. Die Information

A. Dimensions:	44 X 31 mils
B. Passivation:	Si ₃ N ₄ /SiO ₂ (Silicon nitride/ Silicon dioxide)
C. Interconnect:	Al/0.5%Cu with Ti/TiN Barrier
D. Backside Metallization:	None
E. Minimum Metal Width:	3.0 microns (as drawn)
F. Minimum Metal Spacing:	3.0 microns (as drawn)
G. Bondpad Dimensions:	
H. Isolation Dielectric:	SiO ₂
I. Die Separation Method:	Wafer Saw

V. Quality Assurance Information

- A. Quality Assurance Contacts: Richard Aburano (Manager, Reliability Engineering)
Don Lipps (Manager, Reliability Engineering)
Bryan Preeshl (Vice President of QA)
- B. Outgoing Inspection Level: 0.1% for all electrical parameters guaranteed by the Datasheet.
0.1% For all Visual Defects.
- C. Observed Outgoing Defect Rate: < 50 ppm
- D. Sampling Plan: Mil-Std-105D

VI. Reliability Evaluation

A. Accelerated Life Test

The results of the biased (static) life test are shown in Table 1. Using these results, the Failure Rate (λ) is calculated as follows:

$$\lambda = \frac{1}{\text{MTTF}} = \frac{1.83}{192 \times 4340 \times 160 \times 2} \quad (\text{Chi square value for MTTF upper limit})$$

(where 4340 = Temperature Acceleration factor assuming an activation energy of 0.8eV)

$$\lambda = 6.9 \times 10^{-9}$$

$$\lambda = 6.9 \text{ F.I.T. (60\% confidence level @ 25°C)}$$

The following failure rate represents data collected from Maxim's reliability monitor program. Maxim performs quarterly life test monitors on its processes. This data is published in the Reliability Report found at <http://www.maxim-ic.com/qa/reliability/monitor>. Cumulative monitor data for the S3 Process results in a FIT Rate of 0.04 @ 25C and 0.69 @ 55C (0.8 eV, 60% UCL)

B. E.S.D. and Latch-Up Testing (ESD lot XNFABX001B, Latch-Up lot NNFACX001D)

The MS09 die type has been found to have all pins able to withstand a HBM transient pulse of +/-1500V per Mil-Std 883 Method 3015.7. Latch-Up testing has shown that this device withstands a current of +/-200mA.

Table 1
Reliability Evaluation Test Results

MAX6225BESA+

TEST ITEM	TEST CONDITION	FAILURE IDENTIFICATION	SAMPLE SIZE	NUMBER OF FAILURES	COMMENTS
Static Life Test (Note 1)	Ta = 135°C	DC Parameters	80	0	XNFABB002A, D/C 9730
	Biased	& functionality	80	0	XNFABQ001B, D/C 9636
	Time = 192 hrs.				

Note 1: Life Test Data may represent plastic DIP qualification lots.